



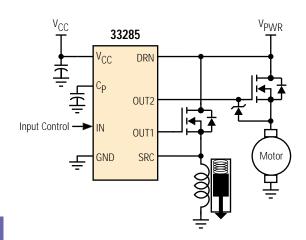
ANALOG PRODUCTS

MC33285 FACT SHEET

33285 DUAL HIGH-SIDE TMOS DRIVER

A single input controls the 33285 in driving two external high-side N-Channel TMOS power FETs controlling incandescent or inductive loads. Pulse Width Modulated input control to 1.0 kHz is possible. The 33285 contains a common internal charge pump used to enhance the Gate voltage of both FETs. An external charge capacitor provides access to the charge pump output. Both external FETs are protected against inductive load transients by separate internal source-to-gate dynamic clamps. The power FETs are protected by the 33285 with over-current delay time of 800 μ S. The device is designed to withstand reverse polarity battery and load dump transients as encountered in automotive applications.

Simplified Application Diagram



APPLICATIONS

- Aircraft Systems
- Automotive Systems
- Robotic Systems
- · Farm Equipment
- Industrial Actuator Control
- Fractional Horsepower DC-Motor Control
- Marine Applications
- Incandescent Lamp Control
- Applications
 Requiring High-Side
 MOSFET Switch Control

CUSTOMER BENEFITS

- Simple solution for operating high-side power FETs at voltages up to 40 V
- Easily used in microprocessor or stand-alone manual circuit applications
- Versatile high-side switching of incandescent or inductive loads
- PWM frequency capable of 1.0 kHz switching
- Reduced PC board space resulting in enhanced reliability and lower costs
- Internal features protect the external power FETs

Performance	Typical Values
Inputs	1
Outputs	2
Operating Voltage	7.0 – 40 V
CP Delivery Current	20 μΑ
PWM Capability	to 1.0 kHz
ESD	± 2000 V
Operating Temp	$-40^{\circ}\text{C} \le \text{T}_{\Delta} \le 125^{\circ}\text{C}$
Junction Operating Temp	$-40^{\circ}\text{C} \le \text{T}_{A} \le 125^{\circ}\text{C}$ $-40^{\circ}\text{C} \le \text{T}_{J} \le 150^{\circ}\text{C}$

FEATURES

- Output control of two external N-channel highside FETs
- Single input control with PWM capability
- 7.0 to 40 V operation
- Over-current latch-OFF protection of external power FET #1
- Over-voltage detection and activation of FET #2 during over-voltage
- Load dump transient protected
- Additional devices available for comparison in Analog Selector Guide SG1002/D

Protection Over Voltage	Detect	Limiting	Latch
	•	•	OFF
FET #1 - Over Current Load Dump	•	•	•

Ordering Information	Package	Ship Method	Motorola Part Number	
Control of the second	8 SOICN	Rail T/R	**33285D **33285DR2	
Data Sheet Order Number			MC33285/D	
Contact Sales for Evaluation Kit Availability				
**Prefix In PC = Eng S		= In Qual; M	1C = Production	

QUESTIONS

- Need a pre-driver IC with internal charge pump to drive two external N-Channel high-side FETs?
- Do you have only a little board space for pre-driver load control?
- Do you need a pre-driver with protection for the two external N-Channel FETs?



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